

Single high-side switch

Datasheet - preliminary data



Features

R _{DS(on)}	Іоит	Vcc
0.060 Ω	0.7 A	65 V

- 8 V to 60 V operating voltage range
- Minimum output current limitation: 0.7 A
- Non-dissipative short-circuit protection (cut-off)
- Programmable cut-off delay time using external capacitor
- Diagnostic signalization for: open load in off-state, cut-off and junction thermal shutdown
- Fast demagnetization of inductive load
- Ground disconnection protection
- V_{CC} disconnection protection
- Undervoltage lock-out
- Designed to meet IEC 61131-2
- PSSO12 package

Applications

- Programmable logic control
- Industrial PC peripheral input/output
- Numerical control machines
- SIL applications

Description

The IPS161H is a monolithic device which can drive capacitive, resistive or inductive loads with one side connected to ground; it is specifically designed to match safety integrity level (SIL) applications.

Built-in thermal shutdown protects the chip against overtemperature and short-circuit. In order to minimize the power dissipation when the output is shorted, a non-dissipative short-circuit protection (cut-off) is implemented, it limits both the output average current value and, consequently, the device overheating. The DIAG common diagnostic pin reports the thermal shutdown, open load in off-state and cut-off.

Cut-off delay time can be programmed by an external capacitor.

Table 1: Device summary

Order code	e Package Packin	
IPS161H	PowerSSO12	Tube
IPS161HTR	PowerSSO12	Tape and reel

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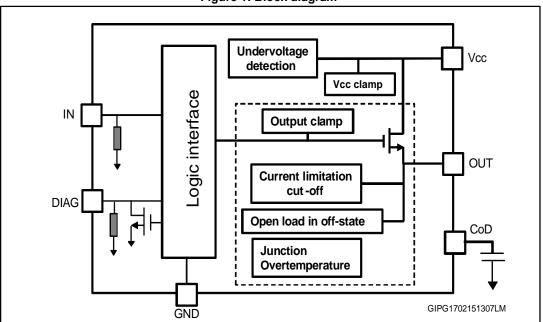
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IPS161H Block diagram

1 Block diagram

Figure 1: Block diagram



Pin description IPS161H

2 Pin description

Figure 2: Pin connection (top view)

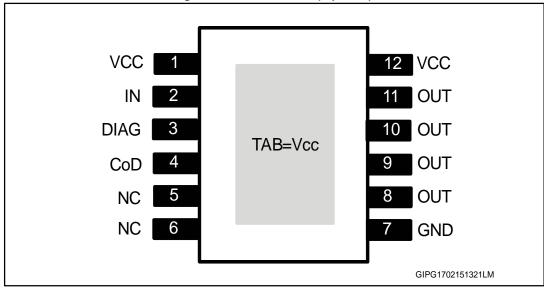


Table 2: Pin configuration

Number	Name	Function	Туре
1, 12, TAB	VCC	Device supply voltage	Supply
2	IN	Channel input	Input
3	DIAG	Common diagnostic pin both for thermal shutdown, cut-off and open load	Output open drain
4	CoD	Cut-off delay pin, cannot be left floating. Connected to GND by 1 k Ω resistor to disable the cut-off function. Connect to a C _{CoD} capacitor to set the cut-off delay see <i>Table 9:</i> "Protection and diagnostic"	Input
5, 6	NC	Not connected	
7	GND	Device ground	Ground
8, 9, 10, 11	OUT	Channel power stage output	Output

2.1 IN

This pin drives the output stage to pin OUT. IN pin has internal weak pull-down resistors, see *Table 8: "Logic inputs"*.

2.2 OUT

Output power transistor is in high-side configuration, with active clamp for fast demagnetization.

IPS161H Pin description

2.3 DIAG

This pin is used for diagnostic purpose and it is internally wired to an open drain transistor. The open drain transistor is turned on in case of junction thermal shutdown, cut-off, or open load in off-state.

2.4 CoD

This pin cannot be left floating and can be used to program the cut-off delay time t_{coff} , see *Table 9: "Protection and diagnostic"* through an external capacitor (C_{CoD}). The cut-off function can be completely disabled connecting the CoD pin to GND through 1 k Ω resistor: in this condition the output channel remains on in limitation condition, supplying the current to the load until the input is forced LOW or the thermal shutdown threshold is triggered or t_{coff} time elapses.

2.5 GND

IC ground.

2.6 VCC

IC supply voltage.

3 Absolute maximum ratings

Table 3: Absolute maximum ratings

Symbol	Parameter	Value	Unit
Vcc	Supply voltage	-0.3 to 65	V
V _{OUT}	Output channel voltage	V _{cc} -V _{clamp} to V _{cc} +0.3	V
I _{IN}	Input current	-10 to +10	mA
Vin	IN voltage	Vcc	V
V_{COD}	Output cut-off voltage pin	5.5	V
Icod	Input current on cut-off pin	-1 to +10	mA
V_{DIAG}	Fault voltage	Vcc	V
IDIAG	Fault current	-5 to +10	
Icc ⁽¹⁾	Maximum DC reverse current flowing through the IC from GND to Vcc	-250	mA
Іоит	Output stage current	Internally limited	
-l _{OUT} ⁽¹⁾	Maximum DC reverse current flowing through the IC from OUT to Vcc	5	А
E _{AS} ⁽¹⁾	Single pulse avalanche energy $(T_{AMB} = 125 \text{ °C}, V_{CC} = 24 \text{ V}, I_{load} = 1.15 \text{ H}$ $load = 24 \text{ Ohm})$ 800		mJ
Ртот	Power dissipation at T _C = 25 °C ⁽²⁾	Internally limited	W
T _{STG}	Storage temperature range	-55 to 150	°C
TJ	Junction temperature	-40 to 150	

Notes:

 $^{^{(2)}(}T_{JSD(MAX)}\text{-}T_C)/\ R_{th(JA)}$



Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. All voltages are referenced to GND.

Table 4: Thermal data

Symbol	Symbol Parameter		Unit
R _{th(JC)}	R _{th(JC)} Thermal resistance junction-case		9000
R _{th(JA)}	Thermal resistance junction-ambient	49	°C/W



Package mounted on a 2-layer application board with Cu thickness = $35 \mu m$, total dissipation area = $1.5 cm^2$ connected by 6 vias.

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 $^{^{(1)}}Verified on application board with <math display="inline">R_{th(ja)}$ = 49 °C/W

4 Electrical characteristics

(8 V < V_{CC} < 60 V; -40 °C < T_{J} < 125 °C, unless otherwise specified)

Table 5: Supply

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Vcc	Supply voltage		Vuvon		60	
Vuvon	Undervoltage on threshold		6.9		8	
V_{UVOFF}	Undervoltage off threshold		6.5		7.8	
Vuvh	Undervoltage hysteresis		0.15	0.5		
	Supply current in off-state	Vcc = 24 V		300	500	
I.		V _{CC} = 60 V		350	600	μA
Is	Complete comment in the state	Vcc = 24 V		1	1.4	Л
	Supply current in on-state	V _{CC} = 60 V		1.4	1.8	mA
I _{LGND}	GND disconnection output current	$V_{GND} = V_{IN} = V_{CC},$ $V_{OUT} = 0 V$			1	mA

Table 6: Output stage

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
D	On-state resistance	Vcc = 24 V, lout = 0.5 A @ T _J = 25 °C		60		mΩ
R _{DS(on)} On-state resistance	Vcc = 24 V, I _{OUT} = 0.5 A @ T _J = 125 °C			120	11122	
Vout(off)	Off-state output voltage	V _{IN} = 0 V and I _{OUT} = 0 A			2	V
	Off state subsuit surrent	$V_{CC} = 24 \text{ V}, V_{IN} = 0 \text{ V},$ $V_{OUT} = 0 \text{ V}$			3	
IOUT(OFF)	Off-state output current	$V_{CC} = 60 \text{ V}, V_{IN} = 0 \text{ V},$ $V_{OUT} = 0 \text{ V}$			10	μA
I _{OUT} (OFF-min)	Off-state output current	$V_{IN} = 0 \text{ V}, V_{OUT} = 4 \text{ V}$	-35		0	

Table 7: Switching (Vcc = 24 V; 125 °C > T_J > -40 °C, R_{LOAD} = 48 Ω)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
tr	Rise time			10		
t _f	Fall time	0.5.4		10		
t _{PD(H-L)}	Propagation delay time off	louт = 0.5 A		20		μs
t _{PD(L-H)}	Propagation delay time on			30		

Electrical characteristics IPS161H

Figure 3: trise and tfall

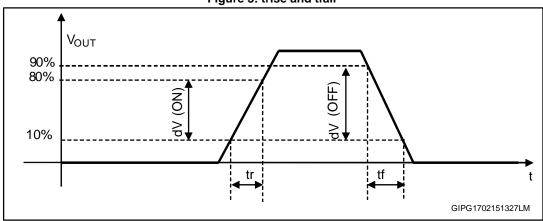


Figure 4: tpD(L-H) and tpD(H-L)

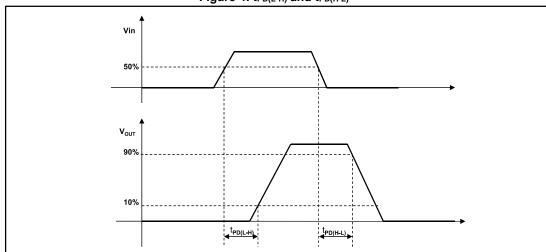


Table 8: Logic inputs

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{IL}	Input low level voltage				0.8	
VIH	Input high level voltage		2.2			V
V _{I(HYST)}	Input hysteresis voltage			0.4		
lin	Input current	Vcc = Vin = 36 V			200	
		Vcc = V _{IN} = 60 V			550	μΑ

Table 9: Protection and diagnostic

3 9						
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{clamp}	V _{CC} active clamp	Icc = 10 mA	65.5	68.5	71.5	
V_{demag}	Demagnetization voltage	I _{OUT} = 0.5 A; Ioad = 1 mH	V _{CC} -71.5	V _{CC} -68.5	V _{CC} -65.5	V
V _{OLoff}	Open load (off-state) or short to V _{CC} detection threshold		2		4	·
t BKT	Open load blanking time				200	μs

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{DIAG}	Voltage drop on DIAG	I _{DIAG} = 4 mA			1	V
	DIAG pin leakage	V _{CC} ≤ 36 V			110	
I _{DIAG}	current	36 V < V _{CC} ≤ 60 V			180	μA
ILIM	Output current limitation	$V_{CC} \le 32 \text{ V},$ $R_{LOAD} \le 10 \text{ m}\Omega$	0.7		1.7	А
t _{coff}	Cut-off current delay time	Programmable by the external capacitor on CoD pin. Cut-off is disabled when CoD pin is connected to GND through 1 k Ω resistor.	50xC _{COD} [nf] ± 35% ⁽¹⁾		μs	
t _{res}	Output stage restart delay time	T _J < T _{JSD}	32xt _{coff} [µs] ± 40%			
TJSD	Junction temperature shutdown		150	170	190	°C
TJHYST	Junction temperature thermal hysteresis			15		

Notes:

 $^{^{(1)}} The$ formula is guaranteed in the range 10 nF $\leq C_{COD} \leq$ 100 nF.

Output logic IPS161H

5 Output logic

Table 10: Output stage truth table

Operation	IN	OUT	DIAG
Normal	L	L	Н
Nomiai	Н	Н	Н
Cut-off	L	L	L
Cut-on	Н	L	L
Overtemperature	L	L	L
	Н	L	L
Open load	L H	H (external pull-up resistor is used)	L (external pull-up resistor is used)
		Н	Н
UVLO	X	L	X
3.20	X	L	X

6 Protection and diagnostic

The IC integrates several protections to ease the design of a robust application.

6.1 Undervoltage lock-out

The device turns off if the supply voltage falls below the turn-off threshold ($V_{UV(off)}$). Normal operation restarts after V_{CC} exceeds the turn-on threshold ($V_{UV(on)}$). Turn-on and turn-off thresholds are defined in *Table 5:* "Supply".

6.2 Overtemperature

The output stage turns off when its internal junction temperature (T_J) exceeds the shutdown threshold T_{JSD}. Normal operation restarts when T_J comes back below the reset threshold (T_{JSD} - T_{JHYST}), see *Table 9: "Protection and diagnostic"*. The internal fault signal is set when the channel is off due to thermal protection and it is reset when the junction triggers the reset threshold. This same behavior is reported on DIAG pin.

6.3 Cut-off

The output current of the power stage is internally limited at the fixed ILIM threshold.

The IPS161H implements the cut-off feature which limits the duration of the current limitation condition.

The duration of the current limitation condition (T_{coff}) can be set by a capacitor (C_{CoD}) placed between CoD and GND pins. The design rule for C_{CoD} is:

 $t_{coff[us]}$ +/- 35% = 50 x $C_{cod[nF]}$

The drift of +/-35% is guaranteed in the range of 10 nF < C_{cod} < 100 nF; lower capacitance than 10 nF can be used.

If I_{LIM} threshold is triggered, the output stage remains in the current limitation condition ($I_{\text{OUT}} = I_{\text{LIM}}$) no longer than t_{coff} . If t_{coff} elapses, the output stage turns off and restarts after the t_{res} restart time.

Thermal shutdown protection has higher priority than cut-off:

- IC is forced off if T_{JSD} is triggered before t_{coff} elapses
- if T_{JSD} is triggered, IC is maintained off even after the t_{res} has elapsed and until the T_J decreases below T_{JSD}-T_{JHYST}

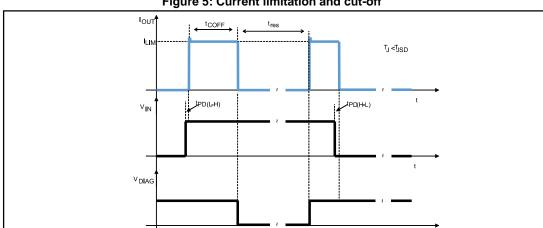


Figure 5: Current limitation and cut-off

The fault condition is reported on the DIAG pin. The internal cut-off flag signal is latched at output switch-off and released after the time tres, the same behavior is reported on DIAG pin.

The status of the DIAG is independent on the IN pin status.

If CoD pin is connected to GND through 1 $k\Omega$ resistor (cut-off feature disabled), when the output channel triggers the limitation threshold, it remains on, in current limitation condition, until the input becomes LOW or the thermal protection threshold is triggered.

In case of low ambient temperature conditions (TAMB < -20 °C) and high supply voltage (Vcc > 36 V) the cut-off function needs activating in order to avoid IC permanent damages. The following table reports the suggested cut-off delay for the different operating voltage.

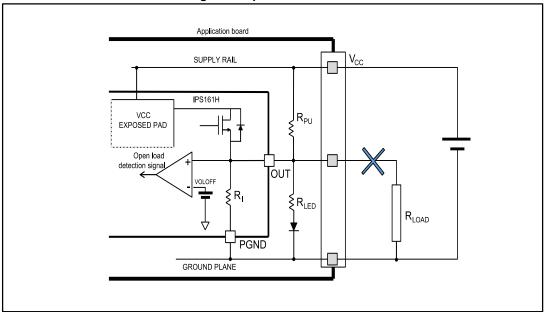
Table 111 minimal dat on dolay for TAMB 1000 than 20 0		
Vcc [V]	Cut-off delay [µs]	Cut-off capacitance [nF]
36-48	100	2.2
48-60	50	1

Table 11: Minimum cut-off delay for TAMB less than -20 °C

6.4 Open load in off-state

The IPS161H provides the open load detection feature which detects if the load is disconnected from the OUT pin. This feature can be activated by a resistor (R_{PU}) between OUT and VCC pins.

Figure 6: Open load off-state



In case of wire break and during the OFF state (IN = low), the output voltage V_{OUT} rises according to the the partitioning between the external pull-up resistor and the internal resistance of the IC (R_I = 115 k Ω).

The effect of the LED (if any) on the output pin has to be considered as well. In case of wire break and during the ON state (IN = high), the output voltage V_{OUT} is pulled up to V_{CC} by the low resistive integrated switch. If the load is not connected, in order to guarantee the correct open load signalization it must result:

 $V_{OUT} > V_{OLoff(max.)}$

Referring to the circuit in figure 6:

$$V_{OUT} = V_{CC} - R_{PU} \times I_{PU} = V_{CC} - R_{PU} \times (I_{RI} + I_{LED} + I_{RL})$$

therefore:

$$R_{PU} < \frac{V_{CC(min)} - V_{OLoff(max)}}{\left(\frac{V_{OLoff(max)} - V_{LED}}{R_I} + \frac{V_{OLoff(max)} - V_{LED}}{R_{LED}}\right)}$$

If the load is connected, in order to avoid any false signalization of the open load, it must result as follows:

 $V_{OUT} < V_{OLoff(min)}$

By taking into account the circuit in figure 6:

$$V_{OUT} = V_{CC} - R_{PU} \times I_{PU} = V_{CC} - R_{PU} \times \left(\frac{V_{OUT}}{R_I} + \frac{V_{OUT} - V_{LED}}{R_{LED}} + \frac{V_{OUT}}{R_L}\right)$$

SO:

$$R_{PU} > \frac{V_{CC(max)} - V_{OLoff(min)}}{\left(\frac{V_{OLoff(min)}}{R_{I}} + \frac{V_{OLoff(min)} - V_{LED}}{R_{LED}} + \frac{V_{OLoff(min)}}{R_{L}}\right)}$$

The fault condition is reported on the DIAG pin and the fault reset occurs when load is reconnected.



If the channel is switched on by IN pin, the fault condition is no longer detected.

When inductive load is driven, some ringing of the output voltage may be observed at the end of the demagnetization. In fact, the load is completely demagnetized when $I_{LOAD}=0$ A and the OUT pin remains floating until next turn-on. In order to avoid a fake signalization of the open load event driving inductive loads, the open load signal is masked for t_{BKT} . So, the open load is reported on the DIAG pin with a delay of t_{BKT} and if the open load event is triggered for more than t_{BKT} .

6.5 V_{CC} disconnection protection

The IC is protected despite the V_{CC} disconnection event. This event is intended as the disconnection of the V_{CC} wire from the application board, see figure below. When this condition happens, the IC continues working normally until the voltage on the V_{CC} pin is $\geq V_{UV(OFF)}$. Once the V_{UVOFF} is triggered, the output channel is turned off independently on the input status. In case of inductive load, if the V_{CC} is disconnected while the output channel is still active, the IC allows the discharge of the energy still stored in the inductor through the integrated power switch.

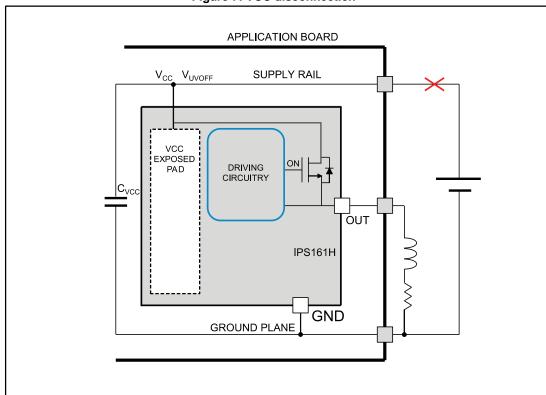
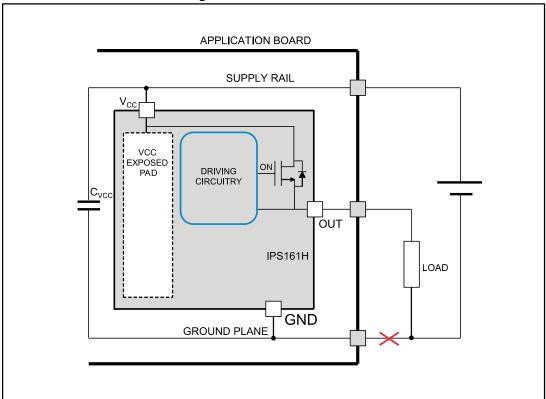


Figure 7: VCC disconnection

6.6 GND disconnection protection

GND disconnection is intended as the disconnection event of the application ground, see figure below. When this event happens, the IC continues working normally until the voltage between V_{CC} and GND pins of the IC results $\geq V_{UVOFF}$. The voltage on GND pin of the IC rises up to the supply rail voltage level. In case of GND disconnection event, a current (I_{LGND}) flows through OUT pin. *Table 8: "Logic inputs"* reports $I_{OUT} = I_{LGND}$ for the worst case of GND disconnection event in case of output shorted to ground.

Figure 8: GND disconnection





Active clamp IPS161H

7 Active clamp

Active clamp is also known as fast demagnetization of inductive loads or fast current decay. When a high-side driver turns off an inductance, an undervoltage is detected on output.

The OUT pin is pulled down to V_{demag} . The conduction state is modulated by an internal circuitry in order to keep the OUT pin voltage at about V_{demag} until the load energy has been dissipated. The energy is dissipated both in IC internal switch and in load resistance.

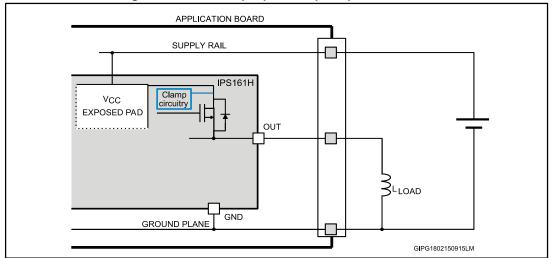
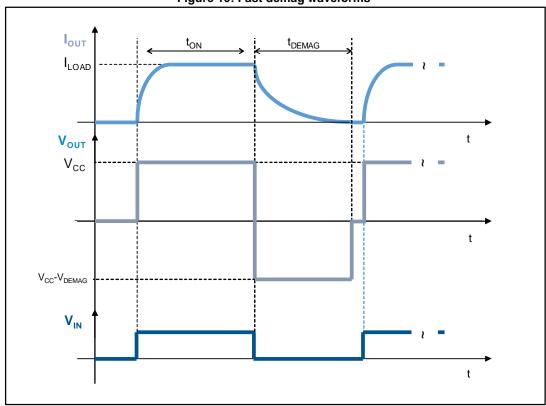


Figure 9: Active clamp equivalent principle schematic





IPS161H Active clamp

> The demagnetization of inductive load causes a huge electrical and thermal stress to the IC. The curve plotted below shows the maximum demagnetization energy that the IC can support in a single demagnetization pulse with $V_{CC} = 24 \text{ V}$ and $T_{AMB} = 125 \,^{\circ}\text{C}$. If higher demagnetization energy is required then an external free-wheeling Schottky diode has to be connected between OUT (cathode) and GND (anode) pins. Note that in this case the fast demagnetization is inhibited.

3500 3000 2500 2000 1500 1000 500 1100

I_{LOAD} [mA]

Figure 11: Typical demagnetization energy (single pulse) at V_{CC} = 24 V and T_{AMB} = 125 °C

Package information IPS161H

8 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

IPS161H Package information

8.1 PowerSSO12 package information

Figure 12: PowerSSO12 package outline

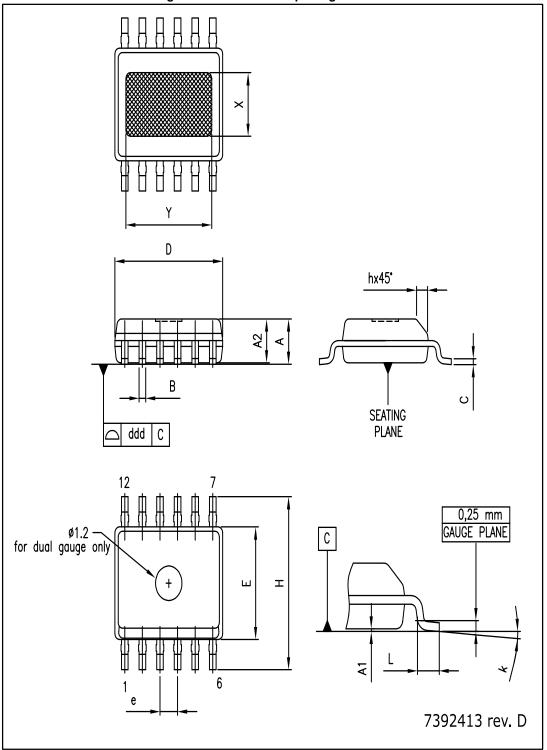


Table 12: PowerSSO12 package mechanical data

Dim		mm	
Dim.	Min.	Тур.	Max.
А	1.250		1.700
A1	0.000		0.100
A2	1.100		1.600
В	0.230		0.410
С	0.190		0.250
D	4.800		5000
Е	3.800		4000
е		0.800	
Н	5800		6.200
h	0.250		0.55
L	0.400		0.1270
k	0d		8d
Х	1.900		2500
Y	3.600		4.200
ddd			0.100



Dimension D doesn't include mold flash protrusions or gate burrs. Mold flash protrusions or gate burrs don't exceed 0.15 mm in total both side.

0.800 0.800 1.550 1.400 3.100 7.565

Figure 13: PowerSSO12 recommended footprint

Revision history IPS161H

9 Revision history

24/25

Table 13: Document revision history

Date	Revision	Changes
10-Jun-2016	1	Initial release.

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